

50 V, 3 A PNP low VCEsat transistor

10 May 2022

1. General description

PNP low $V_{\mbox{CEsat}}$ transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350T-Q

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat} and corresponding low R_{CEsat}
- High collector current capability
- High collector current gain
- Improved efficiency due to reduced heat generation
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Power management applications
- · Low and medium power DC/DC converters
- Supply line switching
- Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-2	А
I _{CRM}		$\delta \le 0.25$; Operated under pulsed conditions; $t_p \le 100$ ms	-	-	-3	A
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	90	135	mΩ

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	E	emitter		С
3	С	collector		B

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS5350T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5350T-Q	ZD%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	А
I _{CRM}	repetitive peak collector current	$\delta \le 0.25$; Operated under pulsed conditions; $t_p \le 100$ ms		-	-3	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	А
I _B	base current			-	-0.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[4]	-	500	mW
			[1] [5]	-	1.2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Operated under pulsed conditions: pulse width tp \leq 100 ms; duty cycle $\delta \leq$ 0.25.

9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	rmal resistance from in free air [1] [2] [3] [4] [1][5]	[1]	-	-	417	K/W
			[2]	-	-	260	K/W
			[3]	-	-	230	K/W
			[4]	-	-	250	K/W
			-	-	104	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	75	-	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

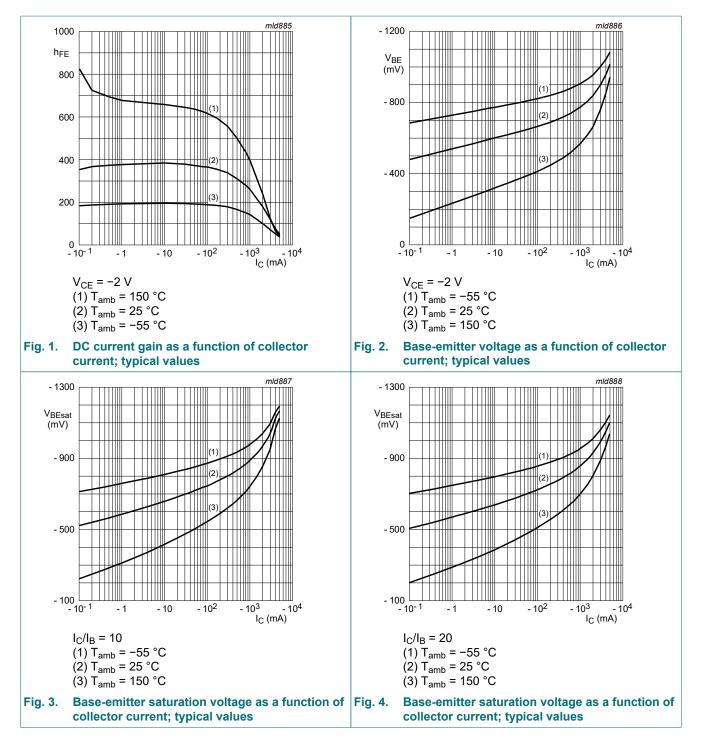
[5] Operated under pulsed conditions: pulse width $t_p \le 100$ ms; duty cycle $\delta \le 0.25$

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I_{C} = -100 µA; I_{E} = 0 A; T_{amb} = 25 °C	-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = -10 mA; I _B = 0 A; T _{amb} = 25 °C	-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	I _E = -100 μA; I _C = 0 A; T _{amb} = 25 °C	-6	-	-	V
I _{сво}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I _C = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I _C = -500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	130	-	-	
		V _{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 µs; T _{amb} = 25 °C	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; t_{p} ≤ 300 μs; δ = 0.02; T_{amb} = 25 °C	-	-	-90	mV
		I _C = -1 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-180	mV
		I_{C} = -2 A; I_{B} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-320	mV
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-270	mV
		I_{C} = -3 A; I_{B} = -300 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-390	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -2 A; I_{B} = -200 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	135	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -2 A; I_{B} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.1	V
		I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-1.2	V
fT	transition frequency	V _{CE} = -5 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	35	pF

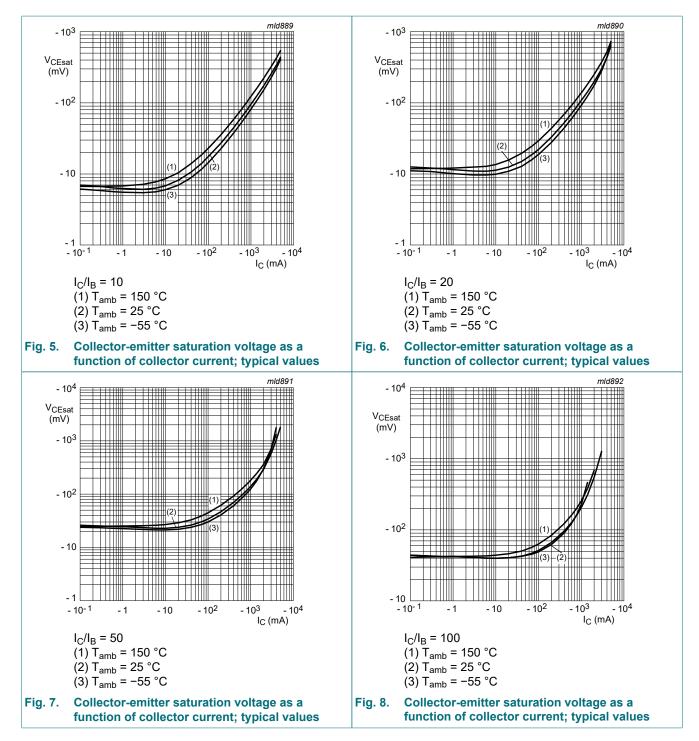
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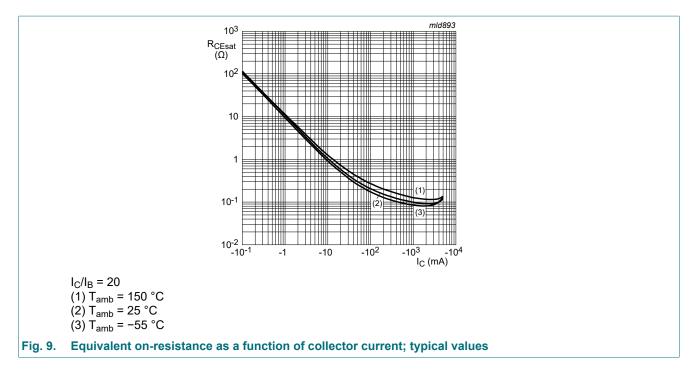


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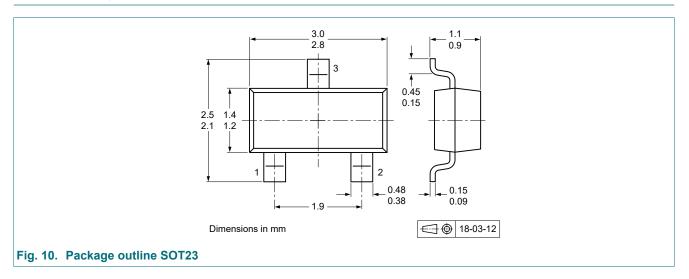


11. Test information

Quality information

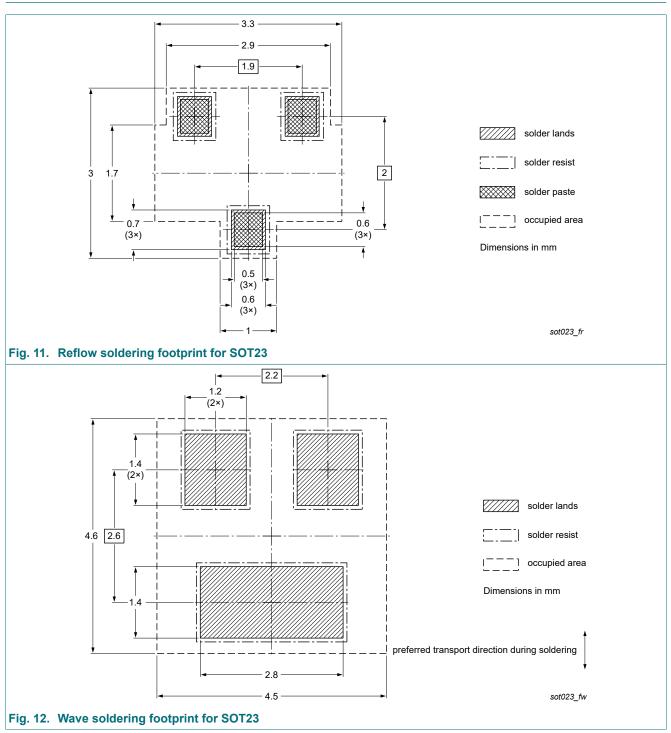
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5350T-Q v.1	20220510	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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